



DSS4160FDB

#### 60V DUAL NPN LOW VCE(SAT) TRANSISTOR

#### Features

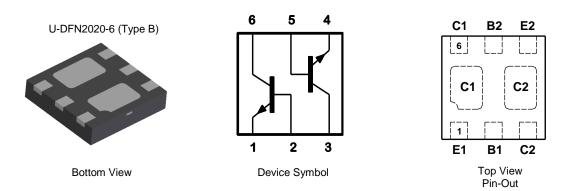
- BV<sub>CEO</sub> > 60V
- I<sub>C</sub> = 1A High Continuous Collector Current
- $R_{CE(SAT)} = 180 m\Omega$  for a Low Equivalent On-Resistance
- Low Saturation Voltage V<sub>CE(SAT)</sub> < 220mV @ 1A</li>
- P<sub>D</sub> up to 2.47W for Power-Demanding Applications
- R<sub>0JA</sub> Efficient, 40% Lower than SOT26
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

# Mechanical Data

- Case: U-DFN2020-6 (Type B)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @
- Weight: 0.0065 grams (Approximate)

### Application

- Load Switches
- Power Management
- Charging Circuits
- Power Switches (e.g. Motors, Fans)



### Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS4160FDB-7	2B	7	8	3,000
DSS4160FDB-7R	2B	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**

Notes:

U-DFN2020-6 (Type B)



2B = Product type Marking Code

Y = Year: 0~9

- W = Week:  $A \sim Z = 1 \sim 26$  Week;
- A~Z = 27~52 Week; Z Represents 52 and 53 Week
- X = A~Z: Internal Code



#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ι <sub>C</sub>	1	А
Peak Pulse Collector Current	ICM	1.5	A
Base Current	Ι <sub>Β</sub>	300	mA
Peak Base Current	I <sub>BM</sub>	1	A

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 5 & 7)		405		
Power Dissignation	(Notes 5 & 8)	D	510	m)\/	
Power Dissipation	(Notes 6 & 7)	PD	1650	mW	
	(Notes 6 & 8)		2470		
	(Notes 5 & 7)		308		
Thermal Desistance Junction to Ambient	(Notes 5 & 8)	D	245	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	R <sub>0JA</sub>	76	·C/w	
	(Notes 6 & 8)		51		
Thermal Resistance, Junction to Lead	(Note 9)	R <sub>θJL</sub>	18	°C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

#### ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Same as Note (5), except the device is mounted with the collector pad on 28mm x 28mm (8cm<sup>2</sup>) 2oz copper.

7. For a dual device with one active die.

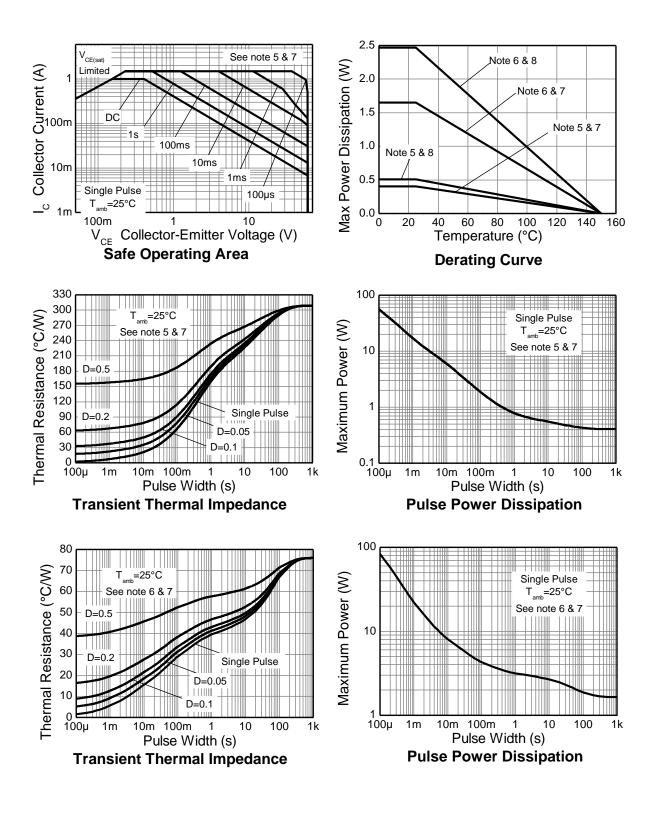
8. For dual device with 2 active die running at equal power.

9. Thermal resistance from junction to solder-point (on the exposed collector pads).

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**



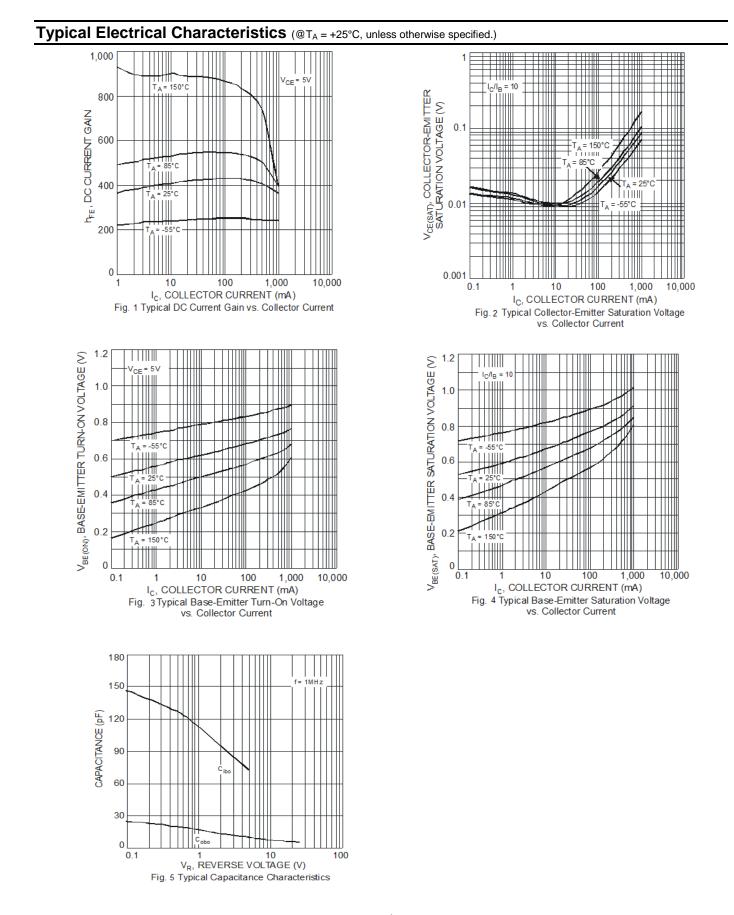


## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	_		V	$I_{\rm C} = 100 \mu {\rm A}$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	60		—	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BVEBO	7			V	I <sub>E</sub> = 100μA
Collector-Base Cutoff Current				100	nA	$V_{CB} = 48V, I_E = 0$
	I <sub>CBO</sub>	_	_	50	μA	V <sub>CB</sub> = 48V, I <sub>E</sub> = 0, T <sub>A</sub> = +150°C
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	100	nA	$V_{EB} = 5.6V, I_C = 0$
		290	430			$V_{CE} = 2V, I_{C} = 100mA$
DC Current Gain (Note 11)	h <sub>FE</sub>	150	220		—	$V_{CE} = 2V, I_{C} = 500mA$
		70	110	_		$V_{CE} = 2V, I_C = 1A$
	V <sub>CE(SAT)</sub>	_	90	120		$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)			170	220	mV	$I_{\rm C} = 1$ A, $I_{\rm B} = 100$ mA
	· · ·		185	240		I <sub>C</sub> = 1A, I <sub>B</sub> = 50mA
Equivalent On-Resistance (Note 11)	R <sub>CE</sub> (SAT)	_	180	240	mΩ	$I_{\rm C} = 500$ mA, $I_{\rm B} = 50$ mA
		_	_	1	V	$I_{\rm C} = 0.5 \text{A}, I_{\rm B} = 50 \text{mA}$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(SAT)}$	_		1.1		$I_{\rm C} = 1$ A, $I_{\rm B} = 50$ mA
		_	_	1.1		I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Base-Emitter Turn-on Voltage (Note 11)	V <sub>BE(ON)</sub>			0.9	V	$V_{CE} = 2V, I_{C} = 0.5A$
Transition Frequency	f <sub>T</sub>	90	175	_	MHz	$V_{CE} = 10V, I_C = 50mA,$ f = 100MHz
Output (Collector) Capacitance	C <sub>OB(C)</sub>	_	4	6	pF	V <sub>CB</sub> = -10V, f = 1MHz
Turn-On Time	t <sub>ON</sub>	_	105		ns	
Delay Time	t <sub>D</sub>	_	15		ns	
Rise Time	t <sub>R</sub>	_	90	_	ns	$V_{\rm CC} = -10V, I_{\rm C} = -0.5A,$
Turn-Off Time	t <sub>OFF</sub>	_	540		ns	$I_{B1} = -I_{B2} = 25 \text{mA}$
Storage Time	ts		410		ns	
Fall Time	tF		130		ns	

Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu s. Duty cycle <math display="inline">{\leq}2\%.$ 

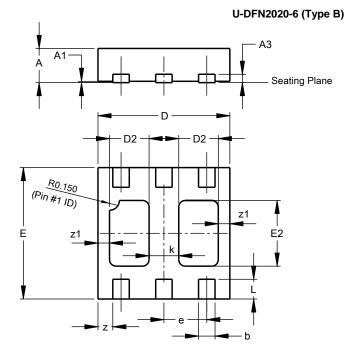






## **Package Outline Dimensions**

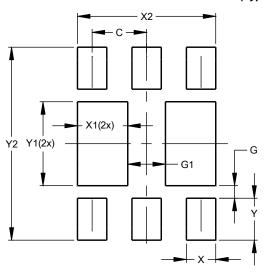
Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN2020-6 Type B					
Dim	Min	Max	Тур			
Α	0.545	0.605	0.575			
A1	0.00	0.05	0.02			
A3	_	_	0.13			
b	0.20	0.30	0.25			
D	1.95	2.075	2.00			
D2	0.50	0.70	0.60			
е	-	-	0.65			
Е	1.95	2.075	2.00			
E2	0.90	1.10	1.00			
k	_	_	0.45			
L	0.25	0.35	0.30			
z	_	_	0.225			
z1	_	_	0.175			
All Dimensions in mm						

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



## U-DFN2020-6 (Type B)

Dimensions	Value		
Dimensions	(in mm)		
С	0.650		
G	0.150		
G1	0.450		
Х	0.350		
X1	0.600		
X2	1.650		
Ý	0.500		
Y1	1.000		
Y2	2.300		



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